L Number	Hits	Search Text	DB	Time stamp
1	86	(tec or thermal near2 expansion near2 coefficient).AB. and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:13
2	2088	(tec or thermal near2 expansion near2 coefficient) near15 (warp$5 or bow$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:14
3	45	(tec or thermal near2 expansion near2 coefficient) near15 (warp$5 or bow$4) same epitax$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:36
4	162	(tec or thermal near2 expansion near2 coefficient) near15 (warp$5 or bow$4) and epitax$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:37
5	26	(tec or thermal near2 expansion near2 coefficient) near15 (warp$5 or bow$4) near10 (reduc$5) and epitax$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:56
6	1	(gaas or gallium near2 arsenide) near10 epitax$5 near10 temperature near10 "1000"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:57
7	43	(gaas or gallium near2 arsenide) near10 temperature near10 "1000"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:59
8	410	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit$5 near10 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 12:02
9	2	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit$5 near10 temperature near5 "650"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 12:01
10	9	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit$5 near10 temperature near5 "600"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 12:02
11	1	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit$5 near10 temperature near5 "550"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 12:02
12	214	((titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit$5 near10 temperature) and @py<2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:32
13	2228	(sin or silicon adj nitride) near10 deposit$5 near10 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:34
14	982	((sin or silicon adj nitride) near10 deposit$5 near10 temperature) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:33

15	1639	(sin or silicon adj nitride) near10 deposit$5 near5 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:34
16	1296	(sin or silicon adj nitride) near5 deposit$5 near5 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:34
17	666	(sin or silicon adj nitride) near5 deposit$5 near2 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:36
18	283	((sin or silicon adj nitride) near5 deposit$5 near2 temperature) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:35
19	0	(sin or silicon adj nitride) near5 deposit$5 near2 temperature near5 "1050"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:36
20	2	(sin or silicon adj nitride) near5 deposit$5 near2 temperature near5 "1000"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:36
21	140	(sin or silicon adj nitride) near5 deposit$5 near2 temperature near5 high	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:40
22	20	thermal near10 (sin or silicon near2 nitride) same (jig or boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:43
23	3	"0713245"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:43
24	8	"713245"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:44
25	98	(sin or silicon near2 nitride) near10 temperature near2 ("1100" or "1000" or "1050" or "1200")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:49
26	47	layered near2 substrate near10 (sapphire or "al.sub.2o.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 14:56
27	27	(sin or silicon near2 nitride or silicon near2 oxide or "sio.sub.2") near10 deposit$5 near2 temperature near5 ("850" or "900" or "950" or "800")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 15:26
28	142	mocvd near10 (gan or gallium adj nitride) near10 (temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 15:28

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29	12	mocvd near10 (gan or gallium adj nitride) near10 epitax$6 near10 (temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 15:29
30	0	(mocvd or movpe) near10 (gan or gallium adj nitride) near10 (temperature) same epitax4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 15:29
31	34	(mocvd or movpe) near10 (gan or gallium adj nitride) near10 (temperature) same epitax$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 17:09
32	0	udea near2 tetsuzo.in. and (warp$ or bow$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 17:10
33	12	ueda near2 tetsuzo.in. and (warp$ or bow$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 17:10
–	353	olsen.in. and bow$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 18:08
–	2	olsen.in. and bow$3 near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 18:09
–	1280	bow$3 near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 18:09
–	38	bow$3 near10 wafer same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 11:05
–	96	bow$3 near10 wafer near10 flat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 13:47
–	687	deposit$ near15 wafer near10 flat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 13:50
–	70	deposit$ near15 wafer near10 (flatten or flattening or flattens)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 13:50
–	3	5562770.URPN.	USPAT	2004/02/10 13:53
–	12	("3458369" | "3808674" | "3821033" | "3997368" | "4079506" | "4159214" | "4415373" | "4631804" | "4805071" | "4830984" | "5158907" | "5319570").PN.	USPAT	2004/02/10 13:54
–	225	direct near5 heat$4 and 117/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:32

–	66	direct near5 heat$4 and 117/$.ccls. and (chemical adj vapor adj deposition or cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:36
–	1911	without near4 heat near2 sink	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:36
–	77	(without near4 heat near2 sink) and (cvd or chemical adj vapor adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:38
–	6	((without near4 heat near2 sink) and (cvd or chemical adj vapor adj deposition)) and 117/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:37
–	5	(without near4 heat near2 sink) same (direct$4 near2 heat$4) and (cvd or chemical adj vapor adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:38
–	38	ueda near2 tetsuzo.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 11:18
–	0	ammonia near10 partial near2 pressure same (anneal$ or heat near2 treat$ or rapid near2 thermal or rta or rtp) same (p$1type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 11:20
–	2	"nh.sub.3" near10 pressure same (anneal$ or heat near2 treat$ or rapid near2 thermal or rta or rtp) same (p$1type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 11:20
–	3	"nh.sub.3" near10 pressure same (anneal$ or heat near2 treat$ or rapid near2 thermal or rta or rtp) same resistiv$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 11:21
–	1	titanium near2 silicide near10 sputter near2 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:02
–	8	(titanium near2 silicide or tisi) same sputter near12 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:02
–	1487	wafer near10 bow$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 16:21
–	40	(wafer near10 bow$5) and (gan or gallium near2 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 16:47
–	224	(wafer near10 bow$5) same flat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 16:58

–	2580	(sin or silicon near2 nitride) near10 (deposit$5 or grow$4) near10 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:00
–	28	(sin or silicon near2 nitride) near10 (deposit$5 or grow$4) near10 temperature near10 "650"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:25
–	119	(gan or gallium near2 nitride) near10 layered near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:27
–	84	(gan or gallium near2 nitride) near10 layered near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:36
–	17	(gan or gallium near2 nitride) near10 layered near2 substrate near10 (sapphire or "al.sub.2o.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:35
–	14	(gan or gallium near2 nitride) near10 layered adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:38
–	109	epitaxial near5 (gan or gallium adj nitride) near10 (deposit$5 or grow$5) near5 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:39
–	25	epitaxial near5 (gan or gallium adj nitride) near10 (deposit$5 or grow$5) near5 temperature same MOCVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:44
–	332	thermal near2 expansion near10 (gan or gallium near2 nitride) near2 coefficient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:45
–	94	thermal near2 expansion near2 (gan or gallium near2 nitride) near2 coefficient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:54
–	120	(gan or gallium near2 nitride) same bow$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 18:01
–	18	(gan or gallium near2 nitride) same bow$5 near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 17:59
–	146	tungsten near2 silicide near10 deposit$5 near5 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 11:02

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